

ABSTRACT

A light-emitting diode in which a protective film and an electrode film formed on the protective film are formed with a uniform thickness and which has high light extraction efficiency, and a method of manufacturing the light-emitting diode are provided. The light-emitting diode has a flat portion and a mesa structure portion including an inclined side surface and a top surface in its upper part. The inclined side surface is formed by wet etching. The protective film includes an electrical conduction window which is provided inside a peripheral region in plane view and is arranged around a light emission hole and from which a portion of the surface of a compound semiconductor layer is exposed. The electrode film is a continuous film that comes into contact with the surface of the compound semiconductor layer exposed from the electrical conduction window, covers at least a portion of the protective film formed on the flat portion, and has the light emission hole on the top surface. A transparent film is formed between a reflecting layer and a compound semiconductor layer. A through-electrode is provided in a range of the transparent film which overlaps the light emission hole.